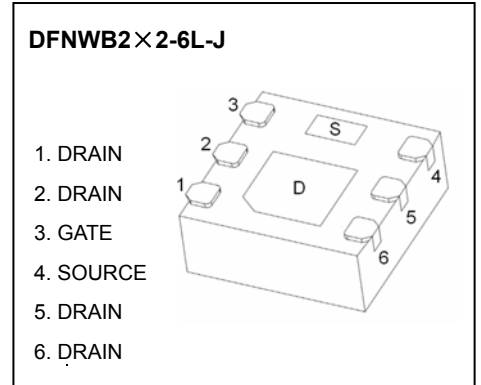


# DFNWB2\*2-6L-J Plastic-Encapsulate MOSFETS

## CJM1216 P-Channel Power MOSFET

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	$I_D$
-12V	21mΩ@-4.5V	-16A
	27mΩ@-2.5V	



### DESCRIPTION

The CJM1216 uses advanced trench technology to provide excellent  $R_{DS(on)}$ , low gate charge and operation with low gate voltage.

This device is suitable for use as a load switching application and a wide variety of other applications.

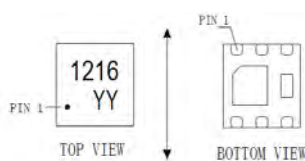
### FEATURES

- Advanced trench MOSFET process technology
- Ultra low on-resistance with low gate charge

### APPLICATIONS

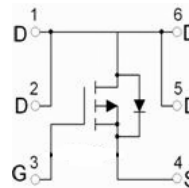
- PWM application
- Load switch
- Battery charge in cellular handset

.....A5F?B;



1216 = Device code  
YY=Code

### Equivalent Circuit



### Maximum ratings ( $T_a=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	-12	V
Gate-Source Voltage	$V_{GS}$	±8	
Drain Current-Continuous	$I_D$	-16	A
Drain Current-Pulsed (note 1)	$I_{DM}$	-65	
Power Dissipation (note 2, $T_a=25^{\circ}C$ )	$P_D$	2.5	W
Maximum Power Dissipation (note 3, $T_c=25^{\circ}C$ )		18	
Thermal Resistance from Junction to Ambient (note 4)	$R_{\theta JA}$	50	$^{\circ}C/W$
Thermal Resistance from Junction to Case (note 4)	$R_{\theta JC}$	6.9	
Junction Temperature	$T_j$	150	$^{\circ}C$
Storage Temperature	$T_{STG}$	-55 ~+150	

# MOSFET ELECTRICAL CHARACTERISTICS

$T_a=25^\circ\text{C}$  unless otherwise specified

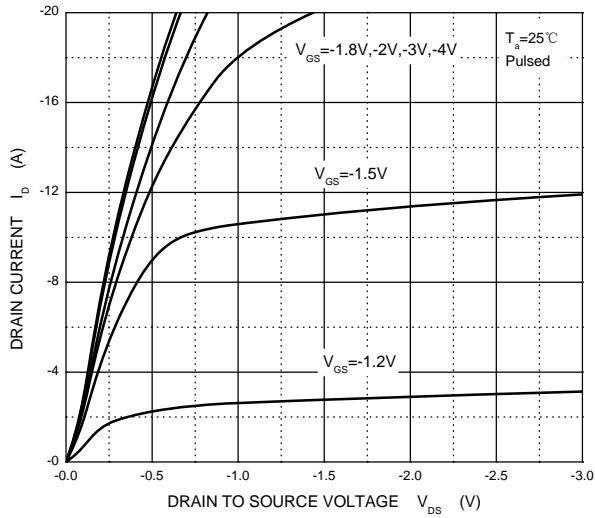
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-12			V
Gate-Body Leakage Current	$I_{GSS}$	$V_{DS} = 0V, V_{GS} = \pm 8V$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -12V, V_{GS} = 0V$			-1	$\mu A$
<b>On Characteristics (note 5)</b>						
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.4	-0.7	-1	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -6.7A$		13	21	m $\Omega$
		$V_{GS} = -2.5V, I_D = -6.2A$		18	27	
Forward Transconductance	$g_{FS}$	$V_{DS} = -10V, I_D = -6.7A$		40		S
<b>Dynamic Characteristics (note 6)</b>						
Input Capacitance	$C_{iss}$	$V_{DS} = -10V, V_{GS} = 0V, f = 1MHz$		2700		pF
Output Capacitance	$C_{oss}$			680		
Reverse Transfer Capacitance	$C_{rss}$			590		
Total Gate Charge	$Q_g$	$V_{DS} = -6V, V_{GS} = -8V, I_D = -10A$		60	100	nC
				35	48	
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -6V, V_{GS} = -4.5V, I_D = -10A$		5		
Gate-Drain Charge	$Q_{gd}$			10		
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Current (note 5)	$I_S$				-16	A
Diode Forward Voltage(note 4)	$V_{SD}$	$V_{GS} = 0V, I_{SD} = -8A$			-1.2	V

**Notes:**

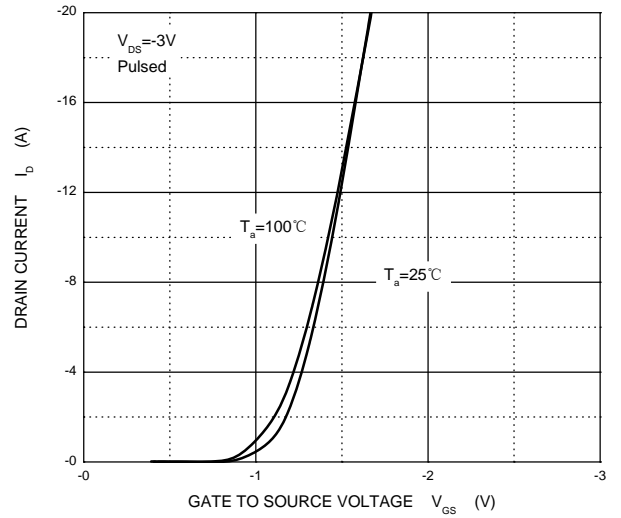
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. This test is performed with no heat sink at  $T_a=25^\circ\text{C}$ .
3. This test is performed with infinite heat sink at  $T_c=25^\circ\text{C}$ .
4. Surface mounted on FR4 board,  $t \leq 10S$ .
5. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
6. Guaranteed by design, not subject to production testing.

# Typical Characteristics

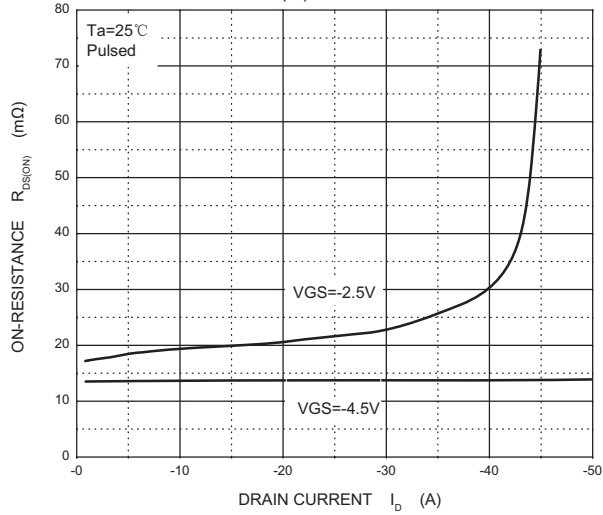
Output Characteristics



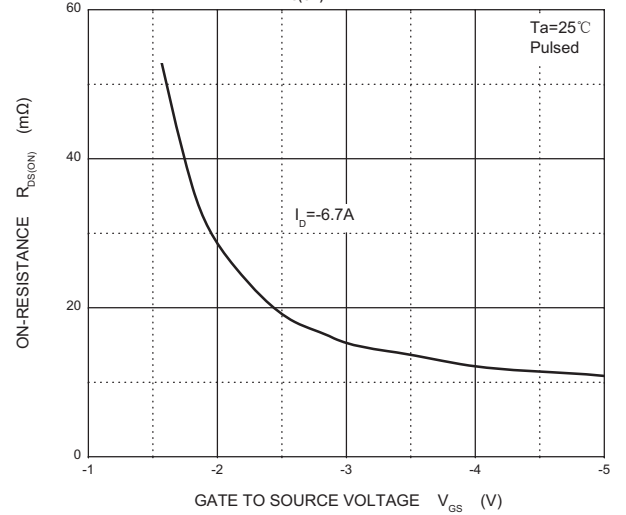
Transfer Characteristics



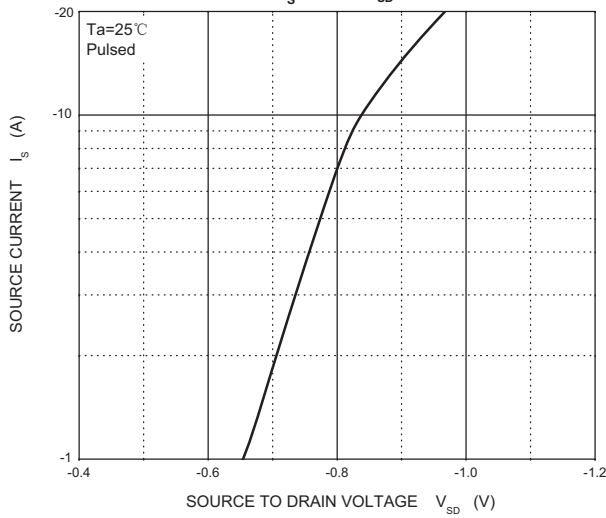
$R_{DS(ON)}$  —  $I_D$



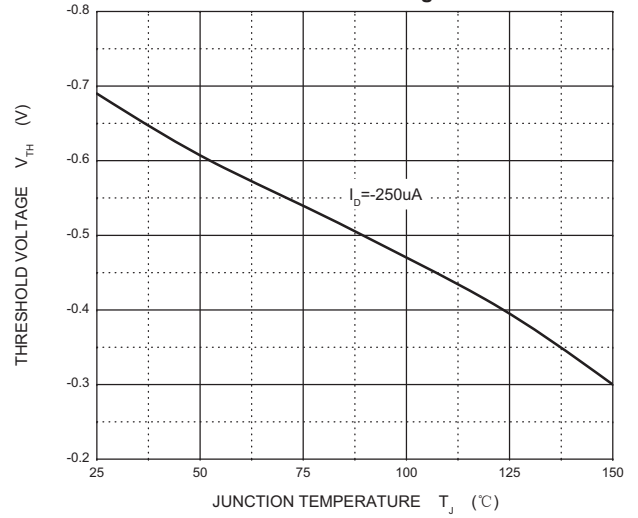
$R_{DS(ON)}$  —  $V_{GS}$



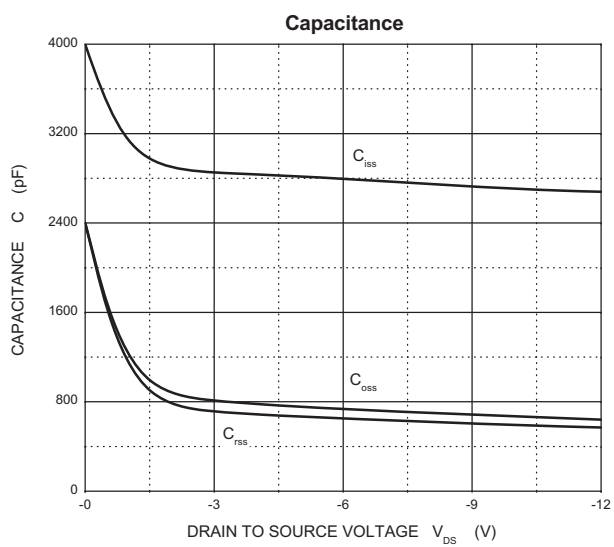
$I_S$  —  $V_{SD}$



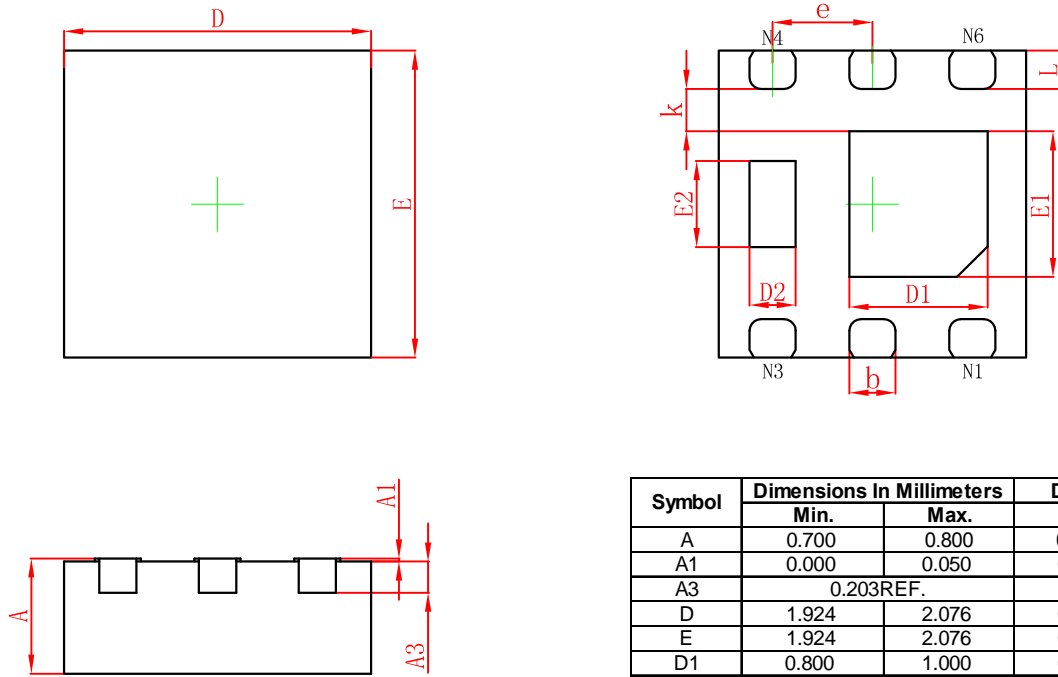
Threshold Voltage



## Typical Characteristics

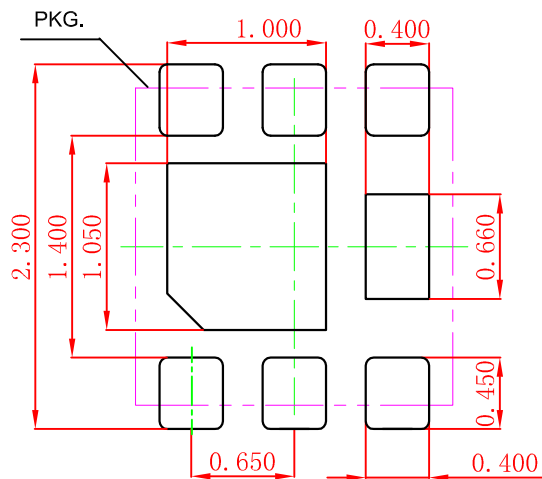


## DFNWB2X2-6L-J Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.800	0.028	0.032
A1	0.000	0.050	0.000	0.002
A3	0.203REF.		0.008REF.	
D	1.924	2.076	0.076	0.082
E	1.924	2.076	0.076	0.082
D1	0.800	1.000	0.031	0.039
E1	0.850	1.050	0.033	0.041
D2	0.200	0.400	0.008	0.016
E2	0.460	0.660	0.018	0.026
k	0.200MIN.		0.008MIN.	
b	0.250	0.350	0.010	0.014
e	0.650TYP.		0.026TYP.	
L	0.174	0.326	0.007	0.013

## DFNWB2X2-6L-J Suggested Pad Layout



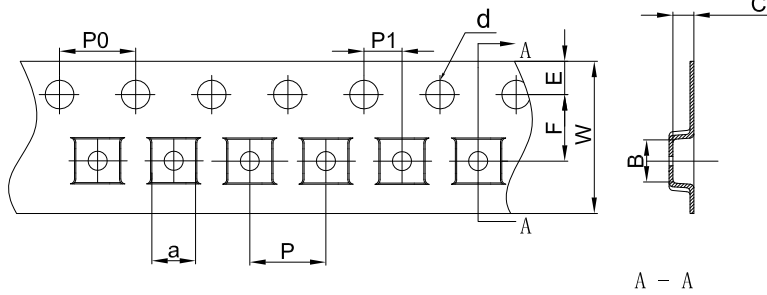
- Note:
1. Controlling dimension: in millimeters.
  2. General tolerance:  $\pm 0.050$ mm.
  3. The pad layout is for reference purposes only.

### NOTICE

JCET reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. JCET does not assume any liability arising out of the application or use of any product described herein.

# DFNWB2X2-6L Tape and Reel

## DFNWB2×2-6L Embossed Carrier Tape



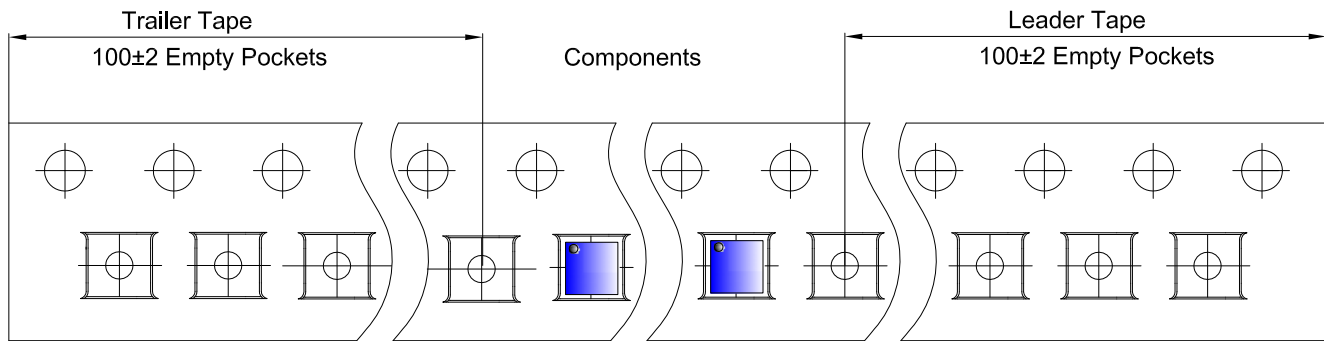
### Packaging Description:

DFNWB2×2-6L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 3,000 units per 7" or 18.0cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

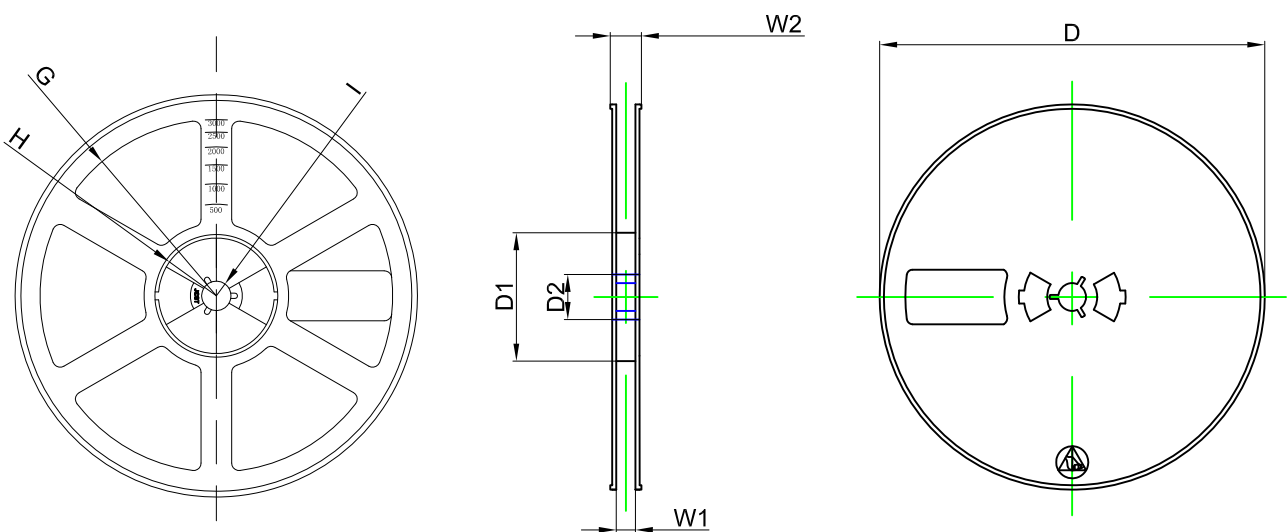
Dimensions are in millimeter

Pkg type	a	B	C	d	E	F	P0	P	P1	W
DFNWB2×2-6L	2.30	2.30	1.10	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

## DFNWB2×2-6L Tape Leader and Trailer



## DFNWB2×2-6L Reel



Dimensions are in millimeter

Reel Option	D	D1	D2	G	H	I	W1	W2
7" Dia	Ø180.00	60.00	13.00	R78.00	R25.60	R6.50	9.50	13.10

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	30,000 pcs	203×203×195	120,000 pcs	438×438×220	